

Thyristor Modules

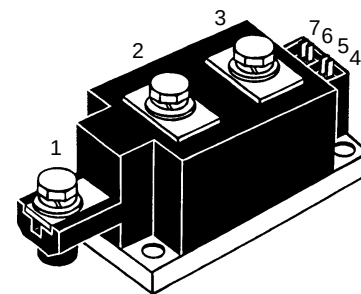
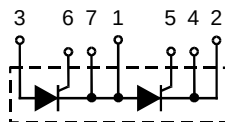
Thyristor/Diode Modules

$$I_{TRMS} = 2 \times 350 \text{ A}$$

$$I_{TAVM} = 2 \times 203 \text{ A}$$

$$V_{RRM} = 1200\text{-}1800 \text{ V}$$

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
1300	1200	MCC 170-12io1
1500	1400	MCC 170-14io1
1700	1600	MCC 170-16io1
1900	1800	MCC 170-18io1



Symbol	Test Conditions		Maximum Ratings	
I_{TRMS}	$T_{VJ} = T_{VJM}$		350	A
I_{TAVM}	$T_C = 85^\circ\text{C}$; 180° sine		203	A
I_{TSM}, I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz)	5400	A
		$t = 8.3 \text{ ms}$ (60 Hz)	5800	A
	$T_{VJ} = T_{VJM}$	$t = 10 \text{ ms}$ (50 Hz)	5000	A
	$V_R = 0$	$t = 8.3 \text{ ms}$ (60 Hz)	5500	A
$\int i^2 dt$	$T_{VJ} = 45^\circ\text{C}$	$t = 10 \text{ ms}$ (50 Hz)	146 000	A ² s
	$V_R = 0$	$t = 8.3 \text{ ms}$ (60 Hz)	140 000	A ² s
	$T_{VJ} = T_{VJM}$	$t = 10 \text{ ms}$ (50 Hz)	125 000	A ² s
	$V_R = 0$	$t = 8.3 \text{ ms}$ (60 Hz)	126 000	A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $f = 50 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 1 \text{ A}$, $di_G/dt = 1 \text{ A}/\mu\text{s}$	repetitive, $I_T = 660 \text{ A}$	100	A/ μs
		non repetitive, $I_T = I_{TAVM}$	500	A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)		1000	V/ μs
P_{GM}	$T_{VJ} = T_{VJM}$	$t_p = 30 \mu\text{s}$	120	W
	$I_T = I_{TAVM}$	$t_p = 500 \mu\text{s}$	60	W
P_{GAV}			20	W
V_{RGM}			10	V
T_{VJ}			-40...+130	°C
T_{VJM}			130	°C
T_{stg}			-40...+125	°C
V_{ISOL}	50/60 Hz, RMS	$t = 1 \text{ min}$	3000	V~
	$I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ s}$	3600	V~
M_d	Mounting torque (M6)		4.5-7/40-62	Nm/lb.in.
	Terminal connection torque (M8)		11-13/97-115	Nm/lb.in.
Weight	Typical including screws		750	g

Features

- International standard package
- Direct copper bonded Al_2O_3 -ceramic with copper base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered E 72873
- Keyed gate/cathode twin pins

Applications

- Motor control, softstarter
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Solid state switches

Advantages

- Simple mounting
- Improved temperature and power cycling
- Reduced protection circuits

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.
IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values
I_{RRM}, I_{DRM}	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	40 mA
V_T, V_F	$I_T, I_F = 600 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.65 V
V_{T0}	For power-loss calculations only ($T_{VJ} = 130^\circ\text{C}$)	0.8 V
r_T		1 mΩ
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	2 V
	$T_{VJ} = -40^\circ\text{C}$	3 V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	150 mA
	$T_{VJ} = -40^\circ\text{C}$	220 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	0.25 V
I_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	10 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 30 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	200 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	150 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 1 \text{ A}; di_G/dt = 1 \text{ A}/\mu\text{s}$	2 μs
t_q	$T_{VJ} = T_{VJM}; I_T = 300 \text{ A}; t_p = 200 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 50 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ. 200 μs
Q_S	$T_{VJ} = 125^\circ\text{C}; I_T, I_F = 300 \text{ A}; -di/dt = 50 \text{ A}/\mu\text{s}$	550 μC
I_{RM}		235 A
R_{thJC}	per thyristor (diode); DC current	0.164 K/W
R_{thJK}	per module	0.082 K/W
	per thyristor (diode); DC current	0.204 K/W
	per module	0.102 K/W
d_s	Creeping distance on surface	12.7 mm
d_a	Creepage distance in air	9.6 mm
a	Maximum allowable acceleration	50 m/s ²

Optional accessories for modules

Keyed Gate/Cathode twin plugs with wire length = 350 mm, gate = yellow, cathode = red

Type ZY 180 L (L = Left for pin pair 4/5) } UL 758, style 1385,

Type ZY 180 R (R = Right for pin pair 6/7) } CSA class 5851, guide 460-1-1

Dimensions in mm (1 mm = 0.0394")

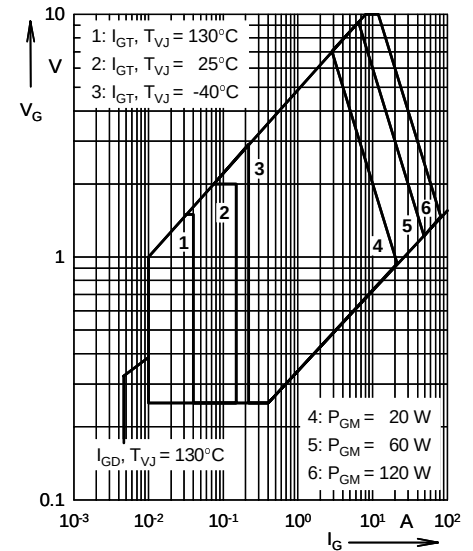
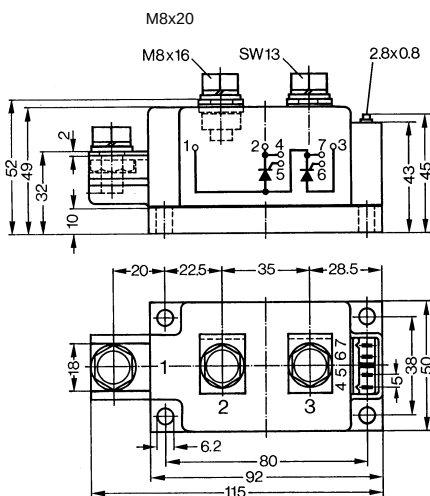


Fig. 1 Gate trigger characteristics

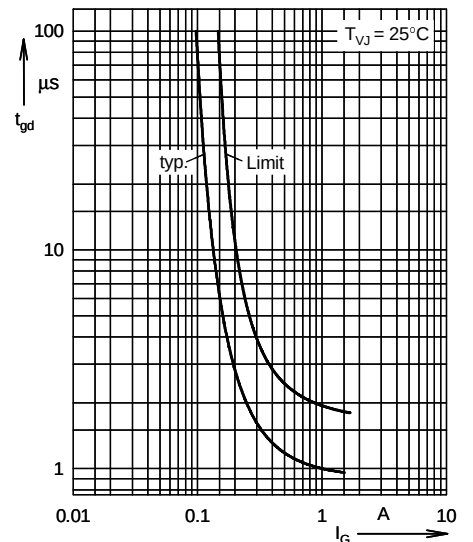


Fig. 2 Gate trigger delay time

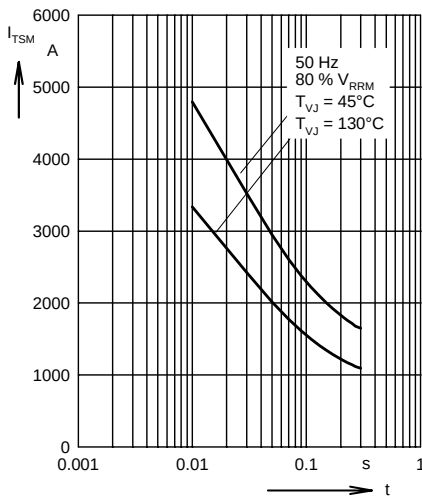


Fig. 3 Surge overload current
 I_{TSM} , I_{FSM} : Crest value, t : duration

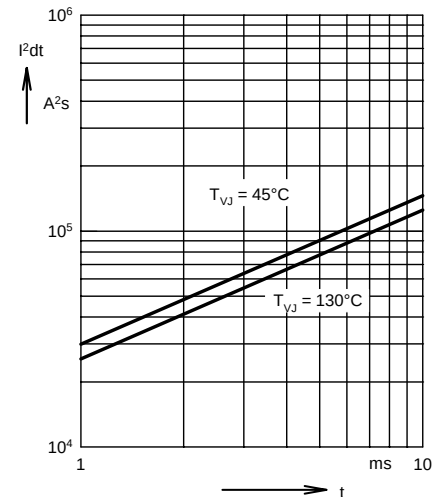


Fig. 4 $\int i^2 dt$ versus time (1-10 ms)

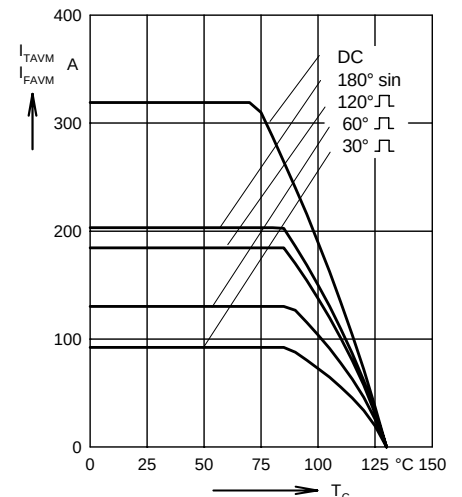


Fig. 4a Maximum forward current at case temperature

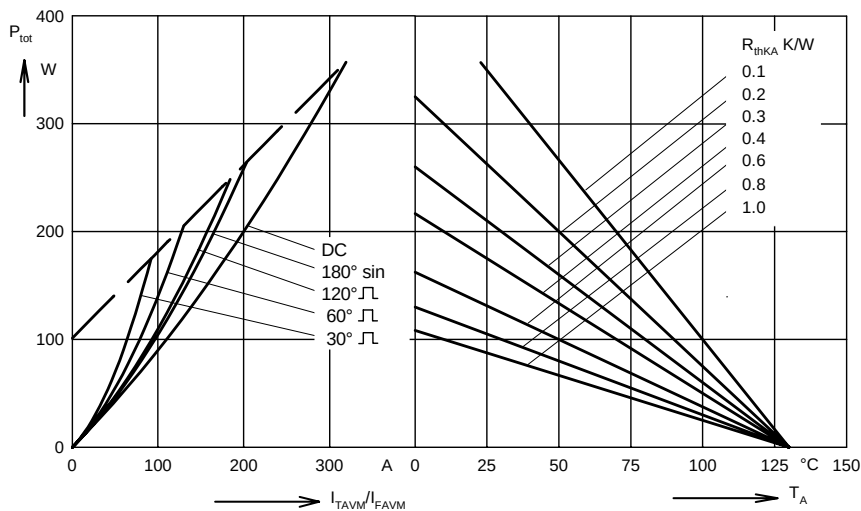


Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

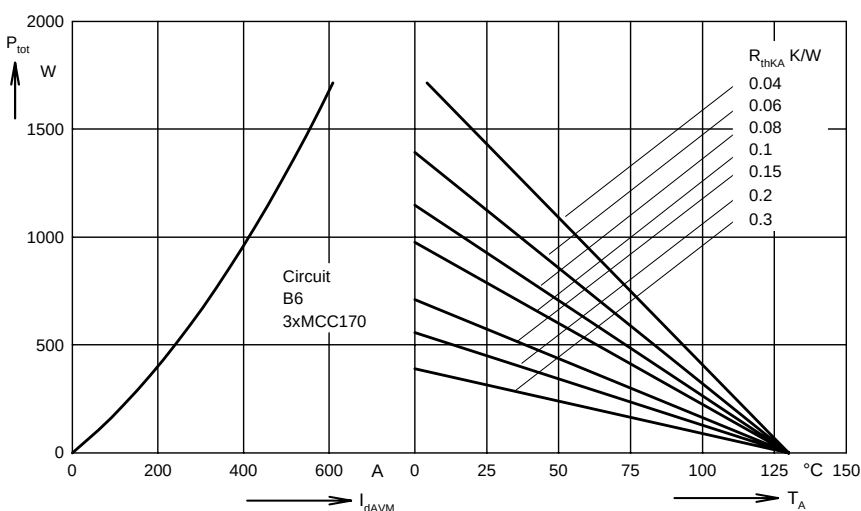


Fig. 6 Three phase rectifier bridge:
 Power dissipation versus direct output current and ambient temperature

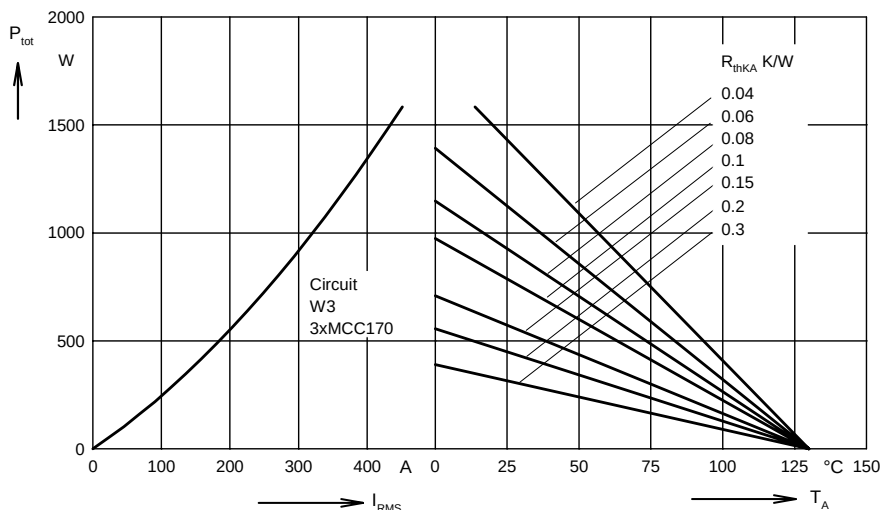


Fig. 7 Three phase AC-controller:
Power dissipation versus RMS
output current and ambient
temperature

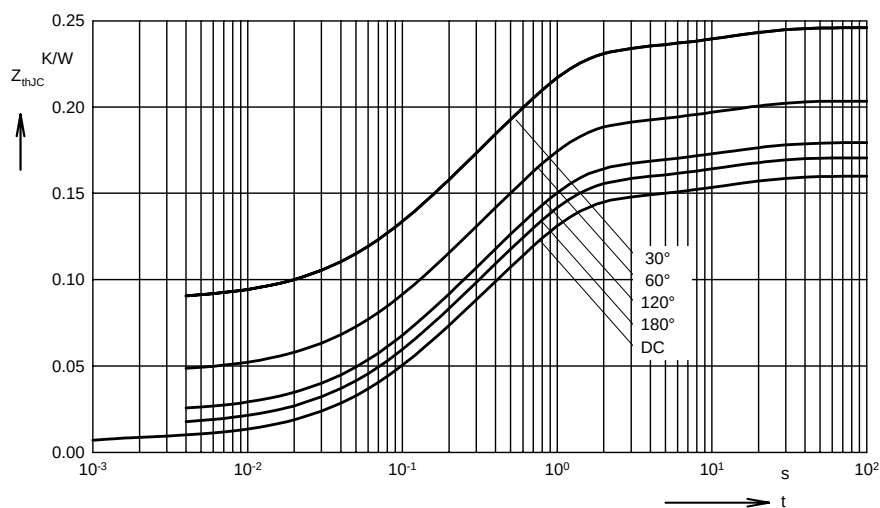


Fig. 8 Transient thermal impedance
junction to case (per thyristor or
diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.160
180°	0.171
120°	0.180
60°	0.203
30°	0.247

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0077	0.00054
2	0.0413	0.098
3	0.096	0.54
4	0.0149	12

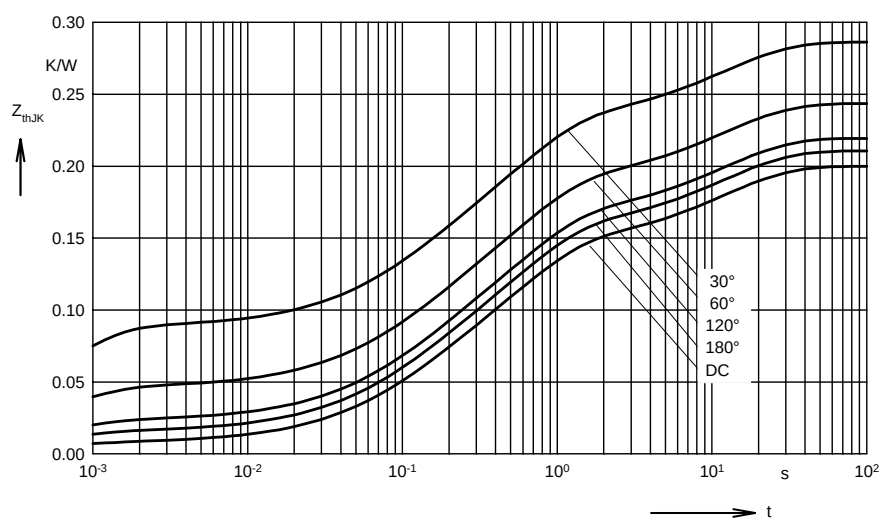


Fig. 9 Transient thermal impedance
junction to heatsink (per thyristor
or diode)

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.200
180°	0.211
120°	0.220
60°	0.243
30°	0.287

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0077	0.00054
2	0.0413	0.098
3	0.096	0.54
4	0.0149	12
5	0.04	12